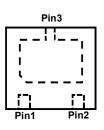


PTVSHC3N10VU

Uni-directional 10V High Capacitance TVS

Description

The PTVSHC3N10VU Transient Voltage Suppressor is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The PTVSHC3N10VU protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. The PTVSHC3N10VU is available in a DFN2×2-3L package with working voltages of 10 volt.



Pin configuration

Feature

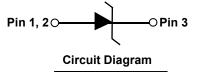
- 6500W Peak pulse power per line (t_P = 8/20µs)
- DFN2×2-3L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD)
 ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

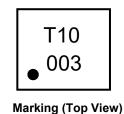
Applications

- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C

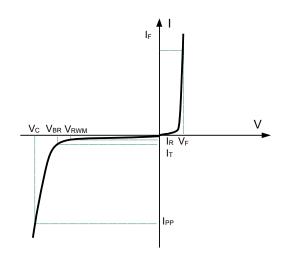




PTVSHC3N10VU

Electronics Parameter

Symbol	Parameter	
VRWM	Peak Reverse Working Voltage	
I _R	Reverse Leakage Current @ V _{RWM}	
V _{BR}	Breakdown Voltage @ I⊤	
Ιτ	Test Current	
I _{PP}	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
P _{PP}	Peak Pulse Power	
CJ	Junction Capacitance	
lF	Forward Current	
VF	Forward Voltage @ I _F	



Electrical characteristics per line@25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}				10	V
Breakdown Voltage	V _{BR}	I _t =1mA	11	12.5	13.5	V
Reverse Leakage Current	I _R	V _{RWM} =10V			1	μA
Maximum Reverse Peak Pulse Current	IPP			240		А
Clamping Voltage	Vc	I _{PP} =20A t _P = 8/20μs		16	17	V
Clamping Voltage	Vc	I _{PP} =90A t _P = 8/20μs		19	21	V
Clamping Voltage	Vc	I _{PP} =200A t _P = 8/20µs		25	26	V
Junction Capacitance	Cj	V _R =0V f = 1MHz		1350	1500	pF

Notes : Measured from pin 3 to pin 1 and pin 2.

Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power ($t_P = 8/20\mu S$)	P _{pp}	6500	W
Lead Soldering Temperature	ΤL	260 (10 sec)	°C
Operating Temperature	TJ	-55 to 150	°C
Storage Temperature	T _{STG}	-55 to 150	°C

PTVSHC3N10VU

Typical Characteristics

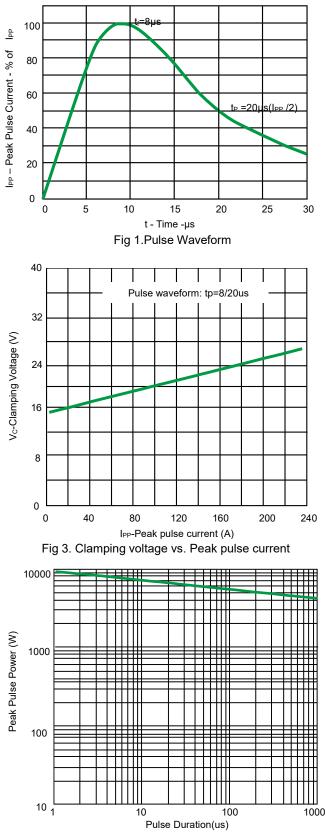
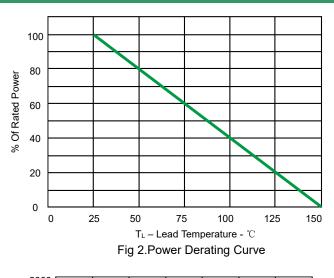
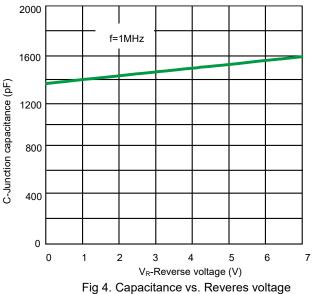


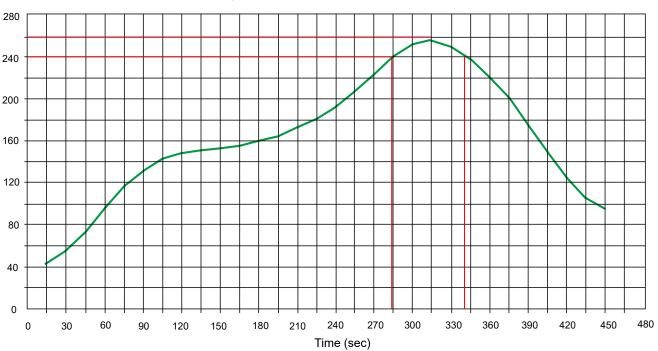
Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time





PTVSHC3N10VU

Solder Reflow Recommendation



Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec

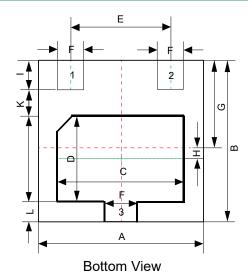
PCB Design

For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- > Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

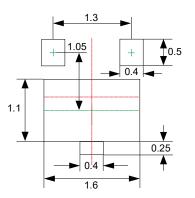
PTVSHC3N10VU

Product dimension (DFN2×2-3L)





Dim	Millimeters		
	MIN	МАХ	
А	1.90	2.10	
В	1.90	2.10	
С	1.40	1.60	
D	0.90	1.15	
E	1.30BSC		
F	0.25	0.40	
G	0.90	1.10	
Н	0.20	0.30	
I	0.32	0.48	
J	0.50	0.65	
К	0.20	0.45	
L	0.15	0.30	



Unit:mm

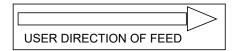
Recommended Soldering Pad

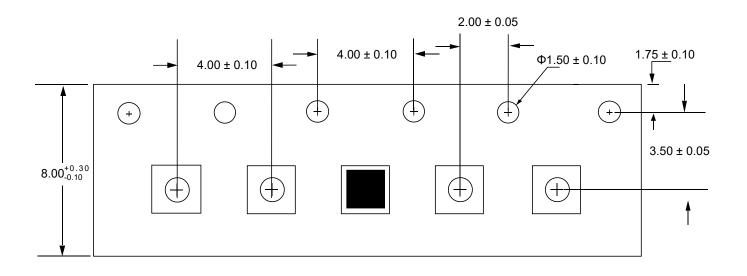
Ordering information

Device	Package	Reel	Shipping
PTVSHC3N10VU	DFN2×2-3L (Pb-Free)	7"	3000 / Tape & Reel

PTVSHC3N10VU

Load with information





IMPORTANT NOTICE

(P) and **Prisemi**[®] are registered trademarks of **Prisemi Electronics Co., Ltd** (Prisemi), Prisemi reserves the right to make changes without further notice to any products herein. Prisemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Prisemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in Prisemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Prisemi does not convey any license under its patent rights nor the rights of others. The products listed in this document are designed to be used with ordinary electronic equipment or devices, Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

Website: http://www.prisemi.com For additional information, please contact your local Sales Representative. ©Copyright 2009, Prisemi Electronics Prisemi® is a registered trademark of Prisemi Electronics.

All rights are reserved.